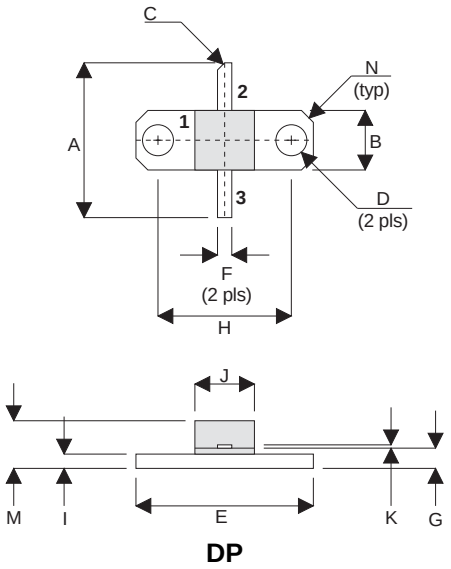
D1014UK

ROHS COMPLIANT METAL GATE RF SILICON FET

MECHANICAL DATA



DP

PIN 1 SOURCE PIN 2 DRAIN

PIN 3 GATE

DIM	mm	Tol.	Inches	Tol.
A	16.51	0.25	0.650	0.010
B	6.35	0.13	0.250	0.005
C	45°	5°	45°	5°
D	3.30	0.13	0.130	0.005
E	18.92	0.08	0.745	0.003
F	1.52	0.13	0.060	0.005
G	2.16	0.13	0.085	0.005
H	14.22	0.08	0.560	0.003
I	1.52	0.13	0.060	0.005
J	6.35	0.13	0.250	0.005
K	0.13	0.03	0.005	0.001
M	5.08	0.51	0.200	0.020
N	1.27 x 45°	0.13	0.050 x 45°	0.005

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 40W – 28V – 500MHz SINGLE ENDED

FEATURES

- **SIMPLIFIED AMPLIFIER DESIGN**
- **SUITABLE FOR BROAD BAND APPLICATIONS**
- **LOW C_{rss}**
- **USEFUL P_O AT 1GHz**
- **LOW NOISE**
- **HIGH GAIN – 12 dB MINIMUM**

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS from 1 MHz to 500 MHz

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

P_D	Power Dissipation	87.5W
BV_{DSS}	Drain – Source Breakdown Voltage	70V
BV_{GSS}	Gate – Source Breakdown Voltage	±20V
$I_{D(sat)}$	Drain Current	10A
T_{stg}	Storage Temperature	–65 to 150°C
T_j	Maximum Operating Junction Temperature	200°C

Semelab plc. Telephone +44(0)1455 556565. Fax +44(0)1455 552612.
E-mail: sales@semelab.co.uk Website: http://www.semelab.co.uk

Document Number 4049
Issue 3

D1014UK

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter		Test Conditions			Min.	Typ.	Max.	Unit
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0	I_D = 100mA		70			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 28V	V_{GS} = 0				2	mA
I_{GSS}	Gate Leakage Current	V_{GS} = 20V	V_{DS} = 0				1	µA
$V_{GS(th)}$	Gate Threshold Voltage*	I_D = 10mA	V_{DS} = V_{GS}		1		7	V
g_{fs}	Forward Transconductance*	V_{DS} = 10V	I_D = 2A		1.6			S
G_{PS}	Common Source Power Gain	P_O = 40W			12			dB
η	Drain Efficiency	V_{DS} = 28V	I_{DQ} = 0.2A		50			%
VSWR	Load Mismatch Tolerance	f = 500MHz			20:1			—
C_{iss}	Input Capacitance	V_{DS} = 0	V_{GS} = –5V	f = 1MHz			120	pF
C_{oss}	Output Capacitance	V_{DS} = 28V	V_{GS} = 0	f = 1MHz			60	pF
C_{rss}	Reverse Transfer Capacitance	V_{DS} = 28V	V_{GS} = 0	f = 1MHz			5	pF

* Pulse Test: Pulse Duration = 300 µs , Duty Cycle ≤ 2%

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

$R_{THj–case}$	Thermal Resistance Junction – Case	Max. 2.0°C / W

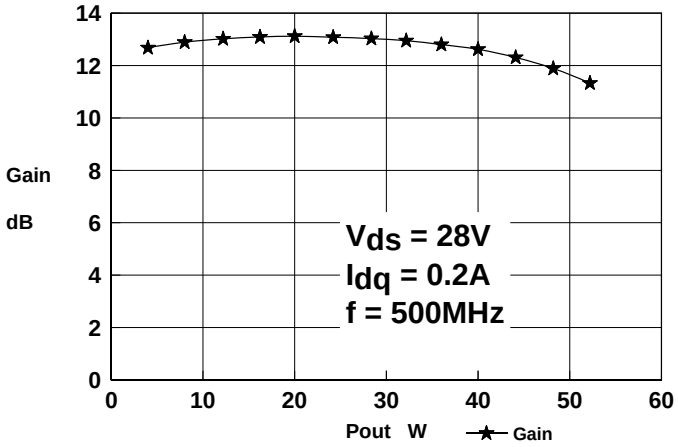


Figure 1- Gain vs. Power Output

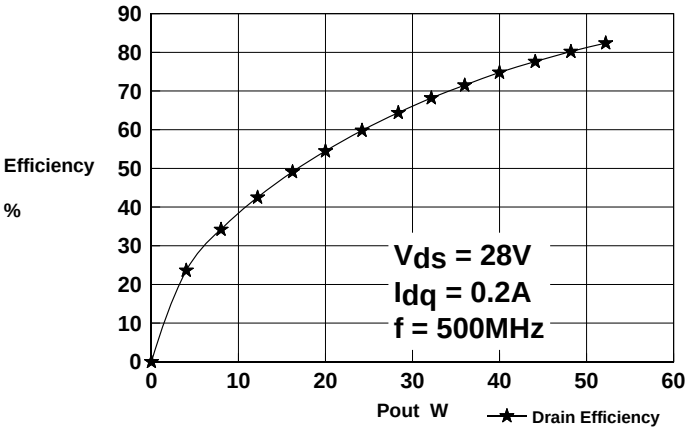


Figure 2 - Efficiency vs Power Output

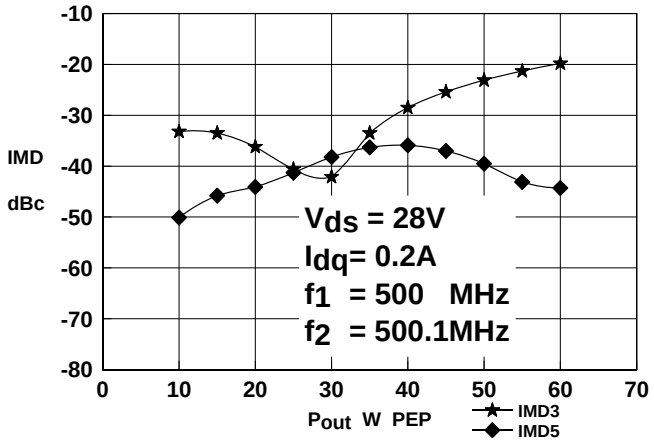


Figure 3 - IMD vs Power Output

OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z_S Ω	Z_L Ω
500MHz	2.3 + j1.0	3.7 + j0.8

Typical S Parameters

! V_{DS} = 28V, I_{DQ} = 0.2A

MHZ S MA R 50

Freq	S11		S21		S12		S22	
MHz	mag	ang	mag	ang	mag	ang	mag	ang
100	0.79	-158	14.62	69	0.012	-7	0.61	-145
200	0.88	-167	5.82	42	0.006	3	0.79	-156
300	0.92	-171	3.02	28	0.007	60	0.87	-162
400	0.92	-176	1.82	18	0.117	77	0.90	-167
500	0.94	-179	1.44	15	0.017	76	0.92	-169
600	0.95	177	1.06	13	0.023	75	0.95	-171
700	0.97	174	0.68	10	0.029	74	0.97	-174
800	0.97	171	0.54	5	0.034	69	0.96	-177
900	0.98	167	0.45	1	0.039	64	0.97	178
1000	0.97	165	0.36	1	0.043	64	0.96	178

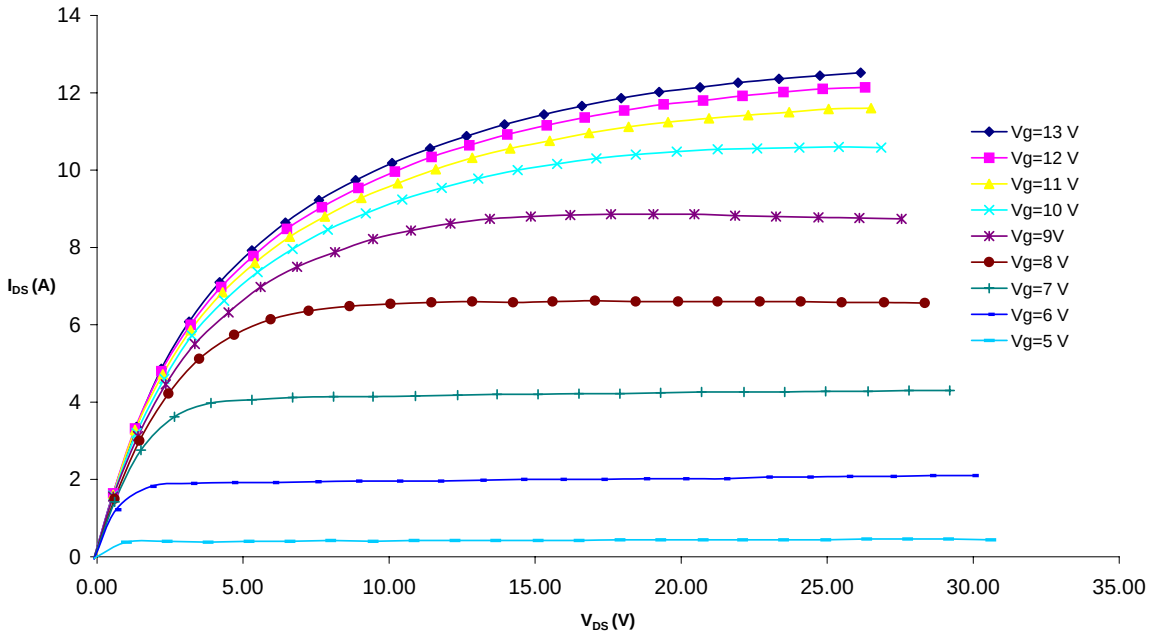


Figure 4 – Typical IV Characteristics.

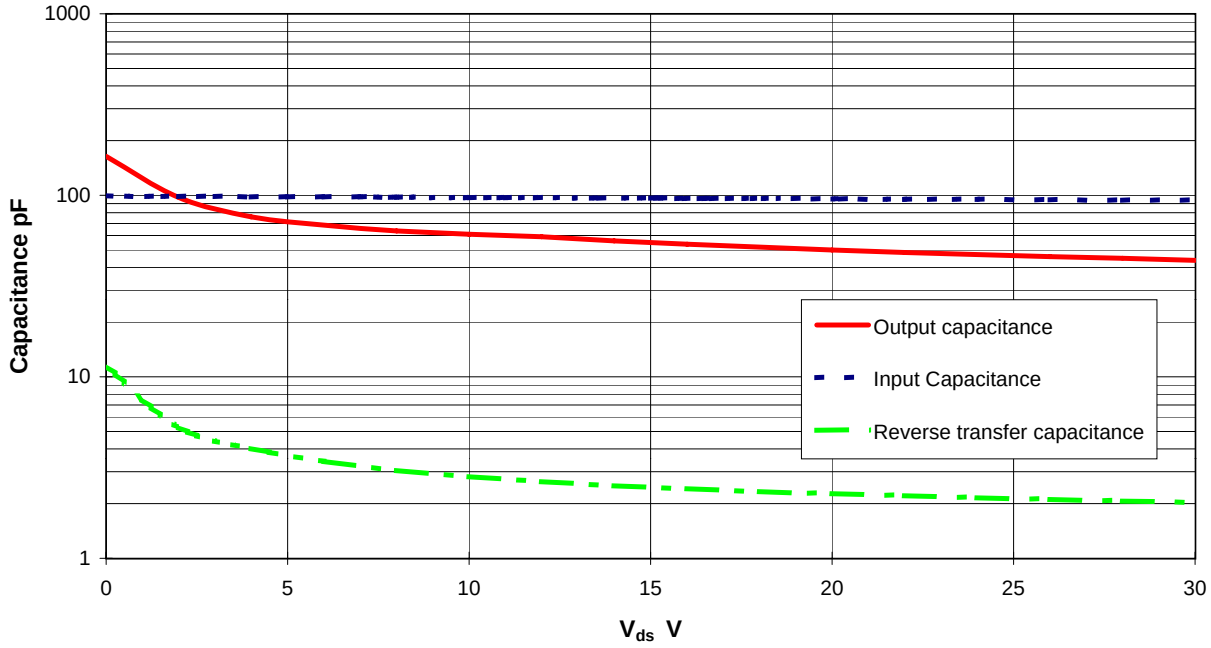
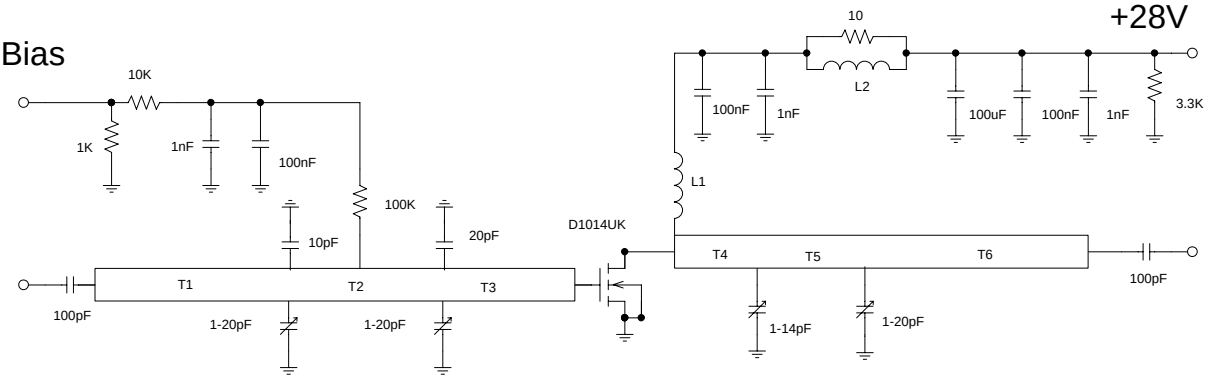


Figure 5 – Typical CV Characteristics.

Gate-Bias



Substrate 0.8mm G200, Er=4.0

All microstrip lines W=1.68mm

T1 36mm
T2 16mm
T3 10mm
T4 6.5mm
T5 12mm
T6 39mm

L1 5.5 turns 20swg enamelled copper wire, 7mm i.d.

L2 1.5 turns 24swg enamelled copper wire on Siemens B62152A7X 2 hole core

D1014UK 500MHz Test Fixture